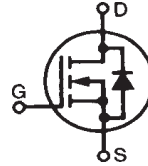


**Linear™ Power
MOSFET w/ Extended
FBSOA**

IXTH12N100L

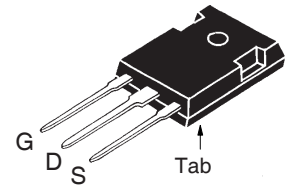
V_{DSS} = 1000V
I_{D25} = 12A
R_{DS(on)} ≤ 1.3Ω

N-Channel Enhancement Mode
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	1000	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	1000	V
V _{GSS}	Continuous	±30	V
V _{GSM}	Transient	±40	V
I _{D25}	T _C = 25°C	12	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	25	A
I _A	T _C = 25°C	12	A
E _{AS}	T _C = 25°C	1.5	J
P _D	T _C = 25°C	400	W
T _J		-55...+150	°C
T _{JM}		150	°C
T _{stg}		-55...+150	°C
T _L	1.6mm (0.063 in.) from Case for 10s	300	°C
T _{SOLD}	Plastic Body for 10s	260	°C
M _d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Package
- Designed for Linear Operation
- Avalanche Rated
- Molding Epoxy Meets UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Programmable Loads
- Current Regulators
- DC-DC Converters
- Battery Chargers
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	1000		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3.5		5.5 V
I _{GSS}	V _{GS} = ±30V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			50 μA 500 μA
R _{DS(on)}	V _{GS} = 20V, I _D = 0.5 • I _{DSS} , Note 1			1.3 Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{DSS}$, Note 1	3.0	5.0	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		2500	pF
C_{oss}			300	pF
C_{rss}			95	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{DSS}$ $R_G = 4.7\Omega$ (External)		30	ns
t_r			55	ns
$t_{d(off)}$			110	ns
t_f			65	ns
$Q_{g(on)}$	$V_{GS} = 20\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{DSS}$		155	nC
Q_{gs}			35	nC
Q_{gd}			55	nC
R_{thJC}			0.31	$^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Safe-Operating-Area Specification

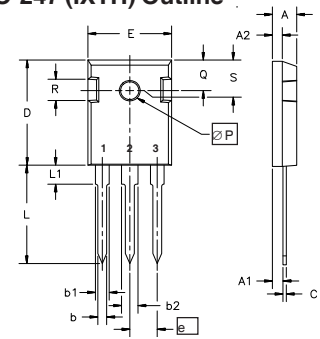
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 800\text{V}$, $I_D = 0.25\text{A}$, $T_C = 60^\circ\text{C}$	200		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			12 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			48 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		1000	ns

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-247 (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

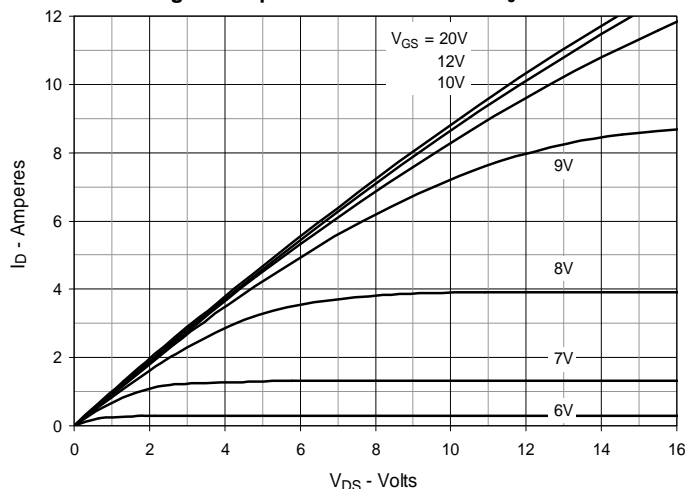


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

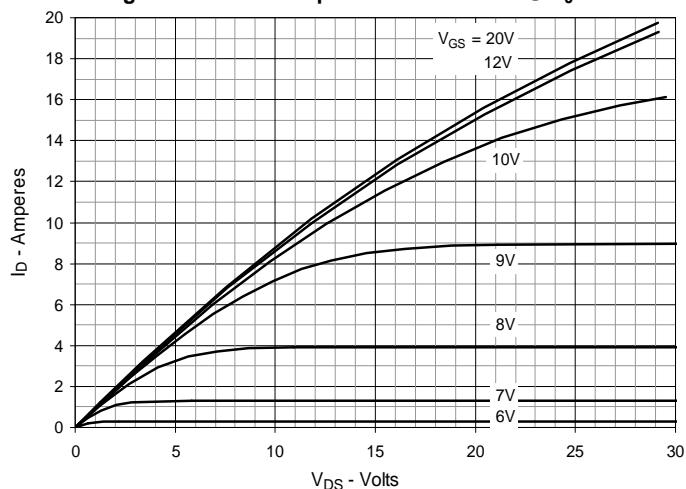


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

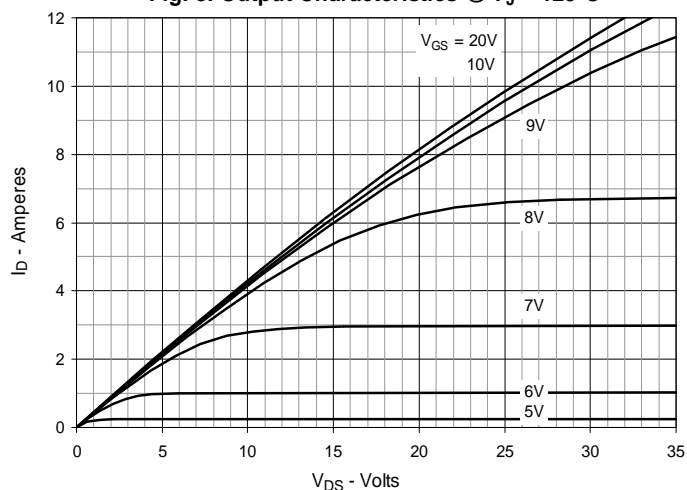


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 6A$ Value vs. Junction Temperature

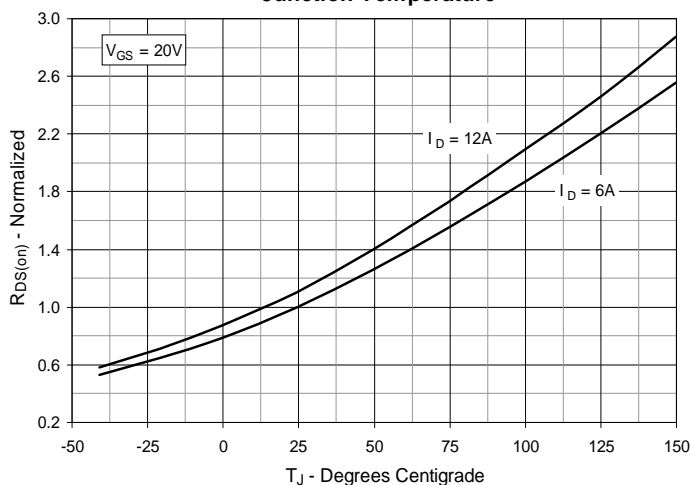


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 6A$ Value vs. Drain Current

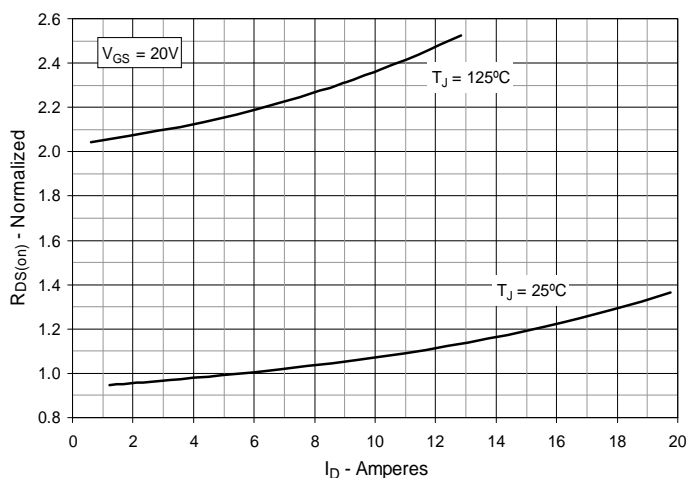


Fig. 6. Maximum Drain Current vs. Case Temperature

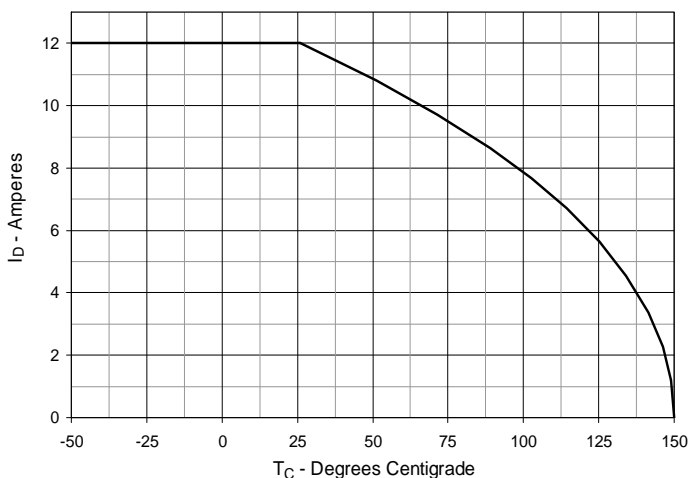


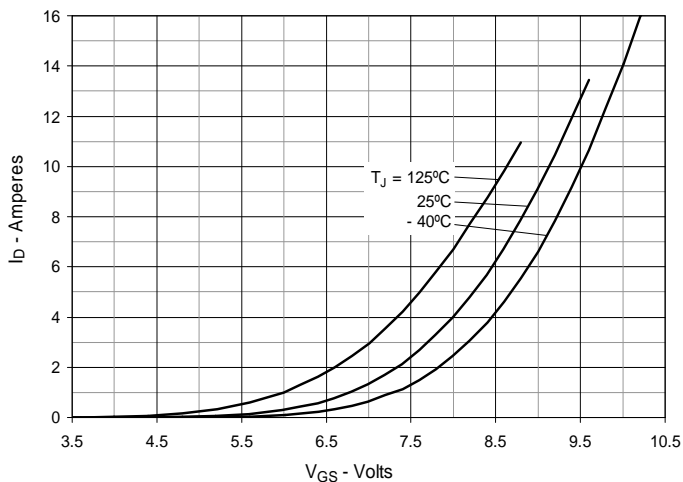
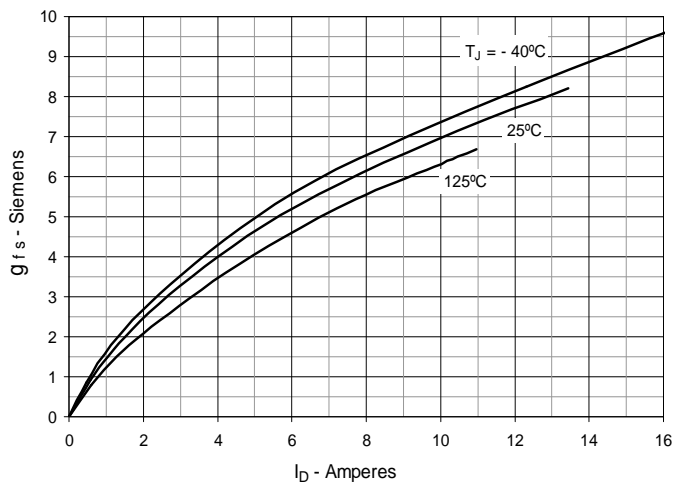
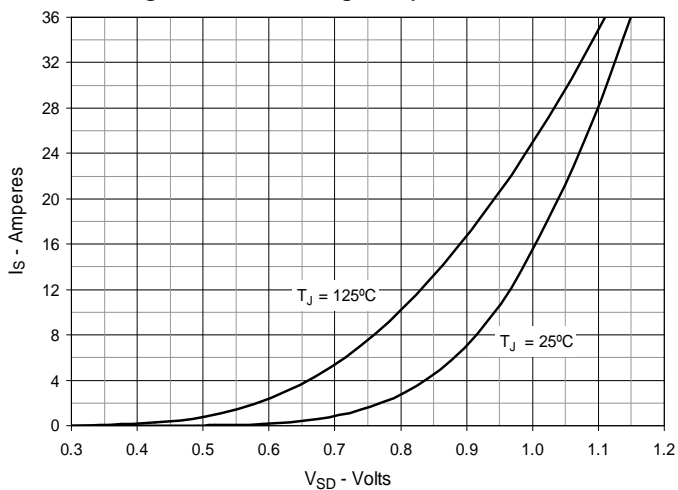
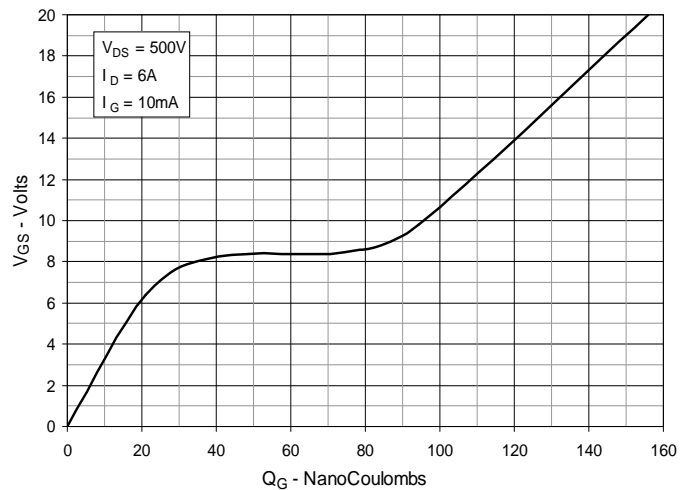
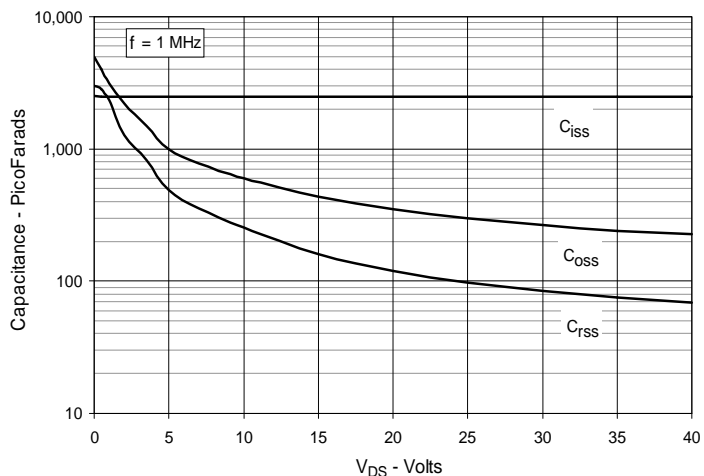
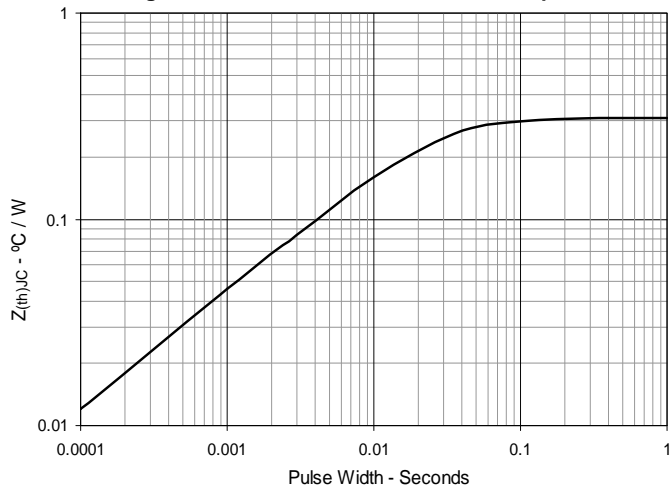
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

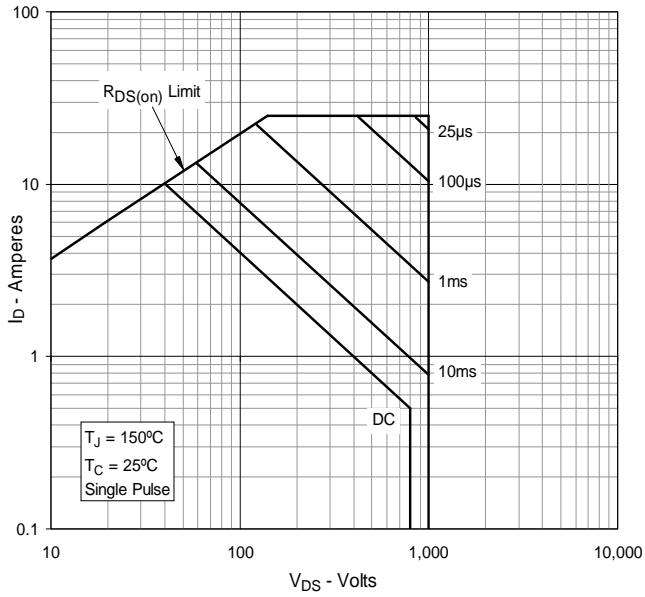


Fig. 14. Forward-Bias Safe Operating Area
@ $T_C = 60^\circ\text{C}$

